VERSION SHOWING THE CHANGES TO THE SPECIFICATION

IN THE SPECIFICATION

Amend the specification as follows:

Page 6, lines 9-12:

Figure 1 shows the simplest embodiment, in which a U-shaped current channel (OFET channel 3) is formed, and figure 2 ~~1b~~) shows a somewhat more elaborate embodiment, in which a meandering OFET channel 3' ~~3~~ is formed.

Page 5, line 35, (and preliminary amendment, page 5, lines 27-37) ~~and~~

Page 5, last line, oscillator[[.]];

Page 6, before line 1, insert the following paragraphs:

- - Fig. 6 is an elevation sectional view of the embodiment of Fig. 1;

and - -

- -Fig. 7 is an elevation sectional view of the embodiment of Fig. 2.- -

Page 7, line 37 to page 8, line 7:

Figure 3 shows one layout for a two-input NOR gate: the layout essentially corresponds to that of the inverter from figure 2B ~~2b~~) with the difference that two drive OFETs are connected in parallel. The second drive OFET comprises the source electrode 14 and has a joint drain electrode 5 with the first drive OFET. The gate electrode 15 of the drive OFET is connected to the second input 12b of the NOR gate. The entire NOR gate is shielded by the two electrodes 1 and 5 which are at the supply voltage or ground.

Page 9, line 3, insert the following paragraphs:

-In Fig. 6, the OFET of Fig. 1 is a schematic representation only of the relative positions of the layers in a sectional elevation view taken from left to right in the figure along a line through the OFET of Fig. 1 that runs from the top of the sheet to the bottom of the sheet. The OFET, from the bottom layer up, comprises a first bottom electrode layer forming electrodes a1 which may comprise respective source and drain electrodes a1 and b1 and which electrodes a1 for example corresponds to the drain electrode 1 and b1 corresponds to the source electrode 2. The OFET also comprises a semiconducting layer e1 over the electrodes a1 and b1 in which semiconducting layer e1 the electrodes 1 and 2 are embedded. The channel 3 of Fig. 1 represents a current channel in the semiconducting layer e1. It can be shown that the current channel 3 of Fig. 1 is produced by such electrodes together with the gate electrode and semiconductor material in the presence of an applied voltage. An insulating layer f1 is over the semiconducting layer e1 and below the second electrode layer c1, the gate electrode layer. The shown second electrode layer c1 is over the insulating layer f1 and forms two gate electrodes c1.

--In Fig. 7, the OFET of Fig. 2 is a schematic representation only of the relative positions of the layers in a sectional elevation view taken from left to right in the figure along a line through the OFET of Fig. 2 that runs from the top of the sheet to the bottom of the sheet. The OFET, from the bottom layer up, comprises a first bottom electrode layer forming lower electrodes

a and b which comprise respective interdigitated source and drain electrodes a and b and which electrodes a correspond to the first electrode 1, Fig. 2. The OFET also comprises a semiconducting layer e over the electrodes a and b in which semiconducting layer e the electrodes 1 and 2 are embedded. The channel 3 of Fig. 2 represents a current channel in the semiconducting layer e. It can be shown that the current channel 3 of Fig. 1 is produced by such electrodes, semiconductor material and the gate electrode above, separated by the insulating layer f. Over the semiconducting layer e is an insulating layer f. A second electrode layer is over the semiconducting layer f which second electrode layer forms the gate electrodes c. - -